	Application No.	Applicant(s)
	10/609,294	KLEM, JOHN F.
Notice of Allowability	Examiner	Art Unit
	Tuan N. Nguyen	2828
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED i) or other appropriate comm IGHTS. This application is	n this application. If not included unication will be mailed in due course. THIS
1. This communication is responsive to <u>06/26/2003</u> .	•	
2. The allowed claim(s) is/are <u>1-23</u> .		
3. \boxtimes The drawings filed on <u>26 June 2003</u> are accepted by the E	xaminer.	
 4. Acknowledgment is made of a claim for foreign priority una) a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: 	e been received. e been received in Application	on No
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the requirements
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which giv		
6. CORRECTED DRAWINGS (as "replacement sheets") must	st be submitted.	
(a) ☐ including changes required by the Notice of Draftsper	son's Patent Drawing Revie	w (PTO-948) attached
1) hereto or 2) to Paper No./Mail Date	·	
(b) ☐ including changes required by the attached Examiner' Paper No./Mail Date	s Amendment / Comment o	r in the Office action of
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the same of		
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT	sit of BIOLOGICAL MAT	ERIAL must be submitted. Note the
 Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 06/26/2003 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	6. Interview S Paper No. 08), 7. Examiner's	nformal Patent Application (PTO-152) Summary (PTO-413), /Mail Date : : Amendment/Comment : Statement of Reasons for Allowance

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ALLOWANCE

Allowable Subject Matter

1. The following is an examiner's statement of reasons for allowance - with respect to claims 1, 12 and 21, the references of the record fail to teach or suggest:

Claim 1:

A distributed Bragg reflector exhibiting high reflectivity for photons of a predetermined energy E and axis, said reflector comprising a stacked plurality of repeat units, each repeat unit comprising a high-index layer, a first interlayer atop said high-index layer, a low-index layer atop said first interlayer, and a second interlayer atop said low-index layer, wherein:

a) said high-index layer is composed essentially of a first material having a first conduction band energy Ec¹, a first valence band energy Ev¹ and first electronic bandgap Eb¹ where electronic bandgap of Eb¹ is greater than predetermined energy E;

- b) said low-index layer is composed essentially of a second material having a second index of refraction which is smaller than said first index of refraction, a second conduction band energy Ec^2 , a second valence Ev^2 and a second electronic bandgap Eb^2 , where said second electronic band Eb^2 being greater than the predetermined energy E;
- c) said first interlayer has a thickness along said predetermined propagation axis not greater than about 10 nanometers, and is composed essentially of a first interlayer material which is characterized by a first interlayer conduction band energy E_c^{IL1} and a first interlayer valence band energy E_v^{IL1} , the energies E_c^{IL1} E_v^{IL1} , E_c^{IL1} E_v^{IL1} , E_c^{IL1} E_v^{IL1} , E_c^{IL1} E_v^{IL1} E_v^{IL1} E_v^{IL1} all being greater than said predetermined energy E_c^{IL1}

d) said second interlayer has a thickness along said predetermined propagation axis not greater than about 10 nanometers, and is composed essentially of a second interlayer material which is characterized by a second interlayer E_c^{IL2} and a second interlayer valence band energy E_v^{IL2} , the energies $E_c^{IL2} \cdot E_v^{IL2} \cdot E_v^{I$

Claim 12:

A distributed Bragg reflector for use at a wavelength near 1.55 gm, comprising a stacked plurality of repeat units with each repeat unit having an optical thickness substantially equal to one-half of the wavelength near 1.55 um, and with each repeat unit comprising a high-index layer consisting essentially of aluminum gallium arsenide antimonide (AlGaAsSb); a first interlayer adjacent the high-index layer; a low-index layer consisting essentially of indium phosphide (InP) adjacent the first interlayer, and a second interlayer adjacent the low-index layer, and with the first and second interlayers each having an energy bandgap greater than 0.82 ev and each acting to substantially prevent optical absorption in the distributed Bragg reflector from spatially indirect photon-assisted transitions between the high-index and low-index layers therein.

Claim 21:

A distributed Bragg reflector with wavelength near 1.55um comprising a plurality of alternating high-index and low-index layers, where *high-index layers* comprising Al_{0.1}Ga_{0.9}As_{0.52}Sb_{0.48} and the *low-index layers* comprising InP; and *an interlayer* comprising AlAs_{0.56}Sb_{0.44} or AlxGa_{1-x}As_{1-y}Sb_y with 0.89<x<1.0 and with 0.44<y< 0.445 *located between*

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each adjacent pair of high-index and low-index layers, by having the exact value of y in this range will provide interlayer a substantial lattice-matching to InP similar with

 $Al_{0.1}Ga_{0.9}As_{0.52}Sb_{0.48}$.

Allowance."

3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for

Communication Information

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tuan N Nguyen whose telephone number is (571) 272-1948. The examiner can normally be reached on M-F: 7:30 - 4:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Harvey Minsun can be reached on (703) 308-16741. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Tuan N. Nguyen

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